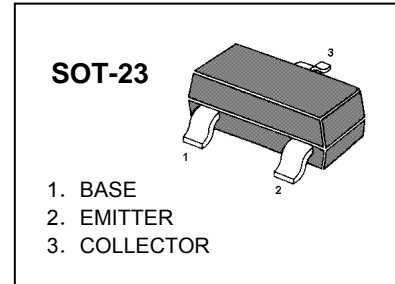


MMBT4401 TRANSISTOR (NPN)
FEATURES

- Epitaxial Planar Die Construction
- Complementary PNP Type Available (MMBT4403)
- Ideal for Medium Power Amplification and Switching

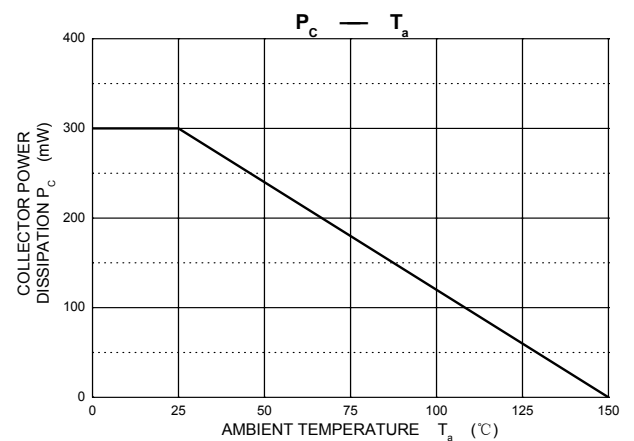
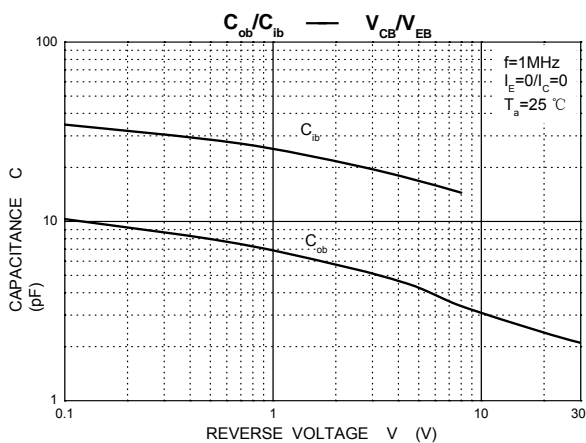
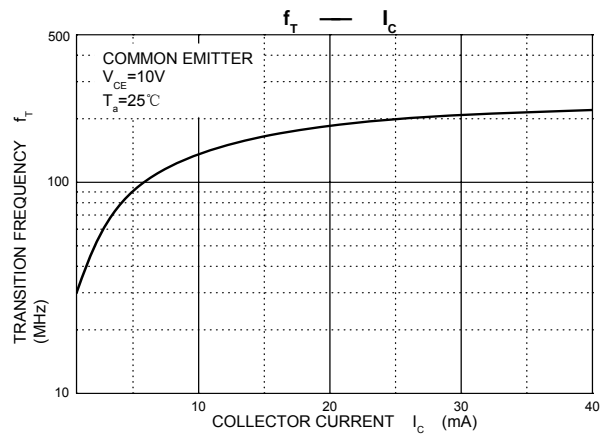
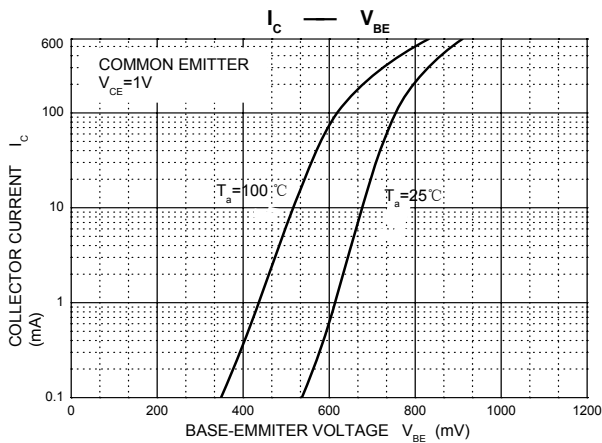
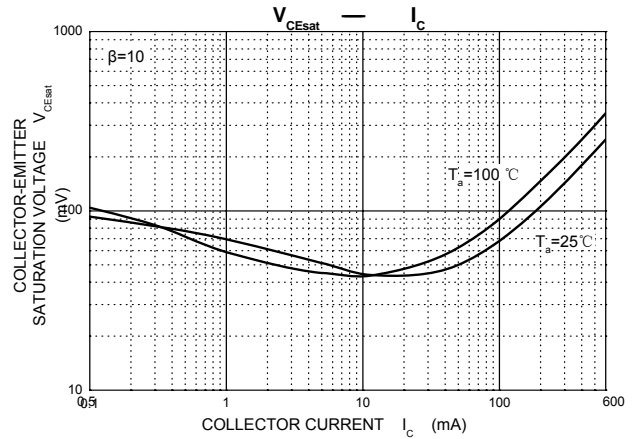
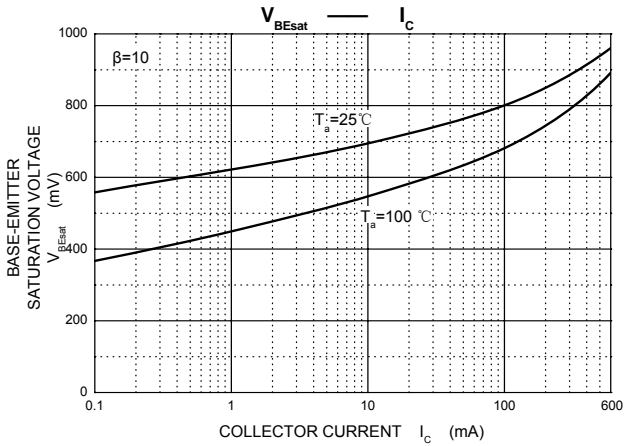
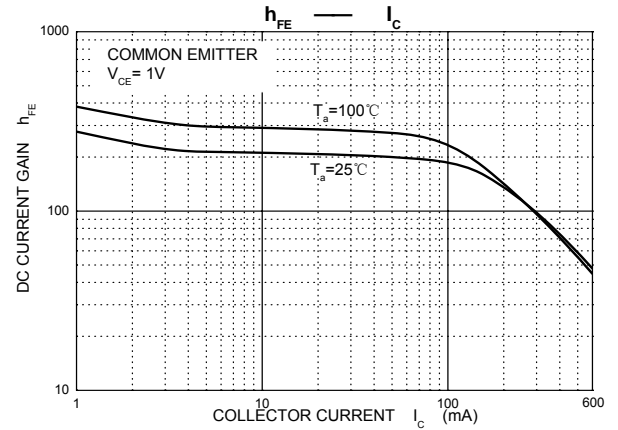
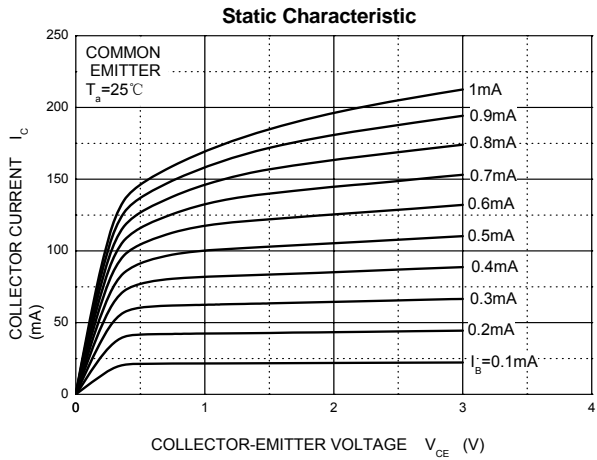

MARKING: 2X
MAXIMUM RATINGS (T_A=25°C unless otherwise noted)

Symbol	Parameter	Value	Units
V _{CB0}	Collector-Base Voltage	60	V
V _{CEO}	Collector-Emitter Voltage	40	V
V _{EBO}	Emitter-Base Voltage	6	V
I _C	Collector Current -Continuous	600	mA
P _C	Collector Power dissipation	0.3	W
T _j	Junction Temperature	150	°C
T _{stg}	Storage Temperature	-55 to +150	°C
R _{θJA}	Thermal Resistance, junction to Ambient	417	°C/mW

ELECTRICAL CHARACTERISTICS (T_{amb}=25°C unless otherwise specified)

Parameter	Symbol	Test conditions	MIN	MAX	UNIT
Collector-base breakdown voltage	V _{(BR)CBO}	I _C = 100μA, I _E =0	60		V
Collector-emitter breakdown voltage	V _{(BR)CEO}	I _C = 1mA, I _B =0	40		V
Emitter-base breakdown voltage	V _{(BR)EBO}	I _E = 100μA, I _C =0	6		V
Collector cut-off current	I _{CBO}	V _{CB} =50 V, I _E =0		0.1	μA
Collector cut-off current	I _{CEO}	V _{CE} =30 V, I _B =0		0.1	μA
Emitter cut-off current	I _{EBO}	V _{EB} =5V, I _C =0		0.1	μA
DC current gain	h _{FE}	V _{CE} =1V, I _C =150mA	100	300	
Collector-emitter saturation voltage	V _{CE(sat)}	I _C =150mA, I _B =15mA		0.4	V
Base-emitter saturation voltage	V _{BE(sat)}	I _C = 150mA, I _B =15mA		0.95	V
Transition frequency	f _T	V _{CE} = 10V, I _C = 20mA f = 100MHz	250		MHz

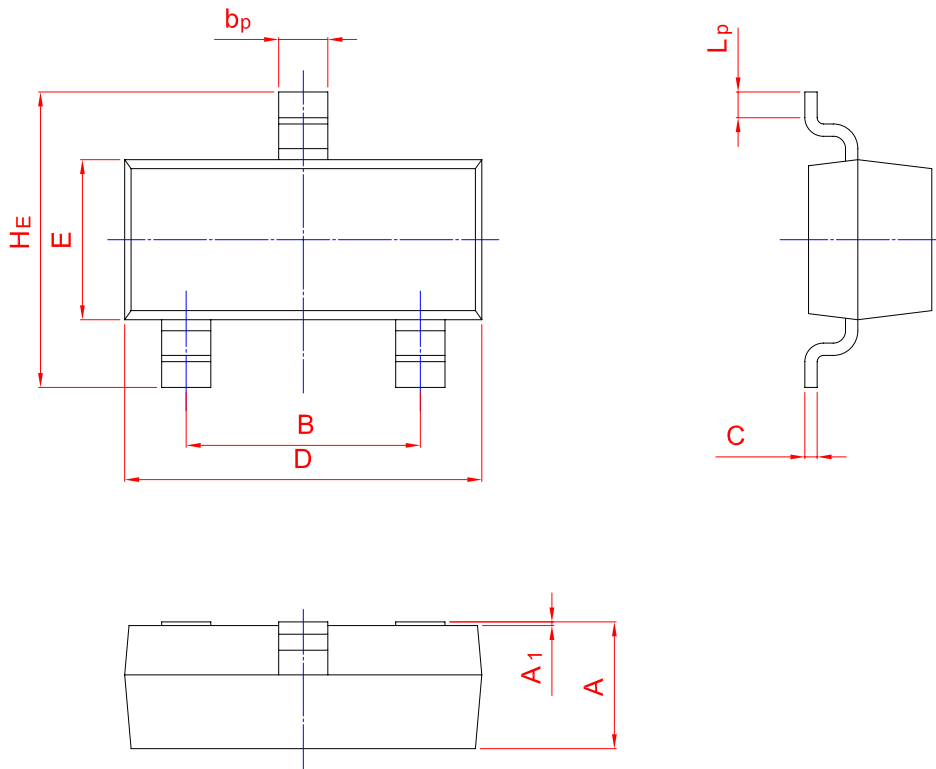
Typical Characteristics



PACKAGE OUTLINE

Plastic surface mounted package; 3 leads

SOT-23



UNIT	A	B	b_p	C	D	E	H_E	A_1	L_p
mm	1.40	2.04	0.50	0.19	3.10	1.65	3.00	0.100	0.50
	0.95	1.78	0.35	0.08	2.70	1.20	2.20	0.013	0.20

单击下面可查看定价，库存，交付和生命周期等信息

[>>TWGMC\(台湾迪嘉\)](#)